L Number	Hits	Search Text	DB	Time stamp
2	2172	(semiconductor adj3 memory) same (cell\$2 adj3 block\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/18 03:01
3	107	((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) same (stor\$2 adj3 data)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 03:00
4	8	(((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) same (stor\$2 adj3 data)) same redundancy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 03:00
5	38	(cell adj3 block) same (stor\$3 adj3 data) same redundancy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18
6	6	((cell adj3 block) same (stor\$3 adj3 data) same redundancy) and ECC	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/18 03:01
7	378	((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 03:01
	4	(((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and redundancy and ECc	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18
9	14	choi-sung-h.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18
10	433	choi-sung-\$.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18
11 .	2	choi-sung.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18
12	0	(((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and ECC and repair	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18
13	118	(((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/18 03:04
14	94	((((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 03:04

				0004/40/40
15	94	1 (((((((((((((((((((USPAT;	2004/10/18
		(cell\$2 adj3 block\$2)) and	US-PGPUB;	03:04
	i ·	365/200,201,225.7.ccls.) and repair) and	EPO; JPO;	
ļ		redundanc\$3) and 365/\$7.ccls.	DERWENT;	
			IBM_TDB	
16	94	(((((semiconductor adj3 memory) same	USPAT;	2004/10/18
İ		(cell\$2 adj3 block\$2)) and	US-PGPUB;	03:04
		365/200,201,225.7.ccls.) and repair) and	EPO; JPO;	
		redundanc\$3) and ((semiconductor adj3	DERWENT;	
		memory) same (cell\$2 adj3 block\$2))	IBM TDB	
17	3		USPĀT;	2004/10/18
		(cell\$2 adj3 block\$2)) and	US-PGPUB;	03:05
İ		365/200,201,225.7.ccls.) and repair) and	EPO; JPO;	
l		redundanc\$3) and (((semiconductor adj3	DERWENT;	
		memory) same (cell\$2 adj3 block\$2)) same	IBM TDB	
		(stor\$2 adj3 data))	_	
18	12		USPAT;	2004/10/18
		data) same redundancy) and	US-PGPUB;	03:05
		(((semiconductor adj3 memory) same	EPO; JPO;	
		(cell\$2 adj3 block\$2)) and	DERWENT;	
		365/200,201,225.7.ccls.)	IBM TDB	
19	8		USPĀT;	2004/10/18
		data) same redundancy) and	US-PGPUB;	03:05
		(((semiconductor adj3 memory) same	EPO; JPO;	
		(cell\$2 adj3 block\$2)) and	DERWENT;	
		365/200,201,225.7.ccls.)) and	IBM TDB	
		(((((semiconductor adj3 memory) same	_	
		(cell\$2 adj3 block\$2)) and		
		365/200,201,225.7.ccls.) and repair) and		*
		365/200,201,225.7.ccls.) and repair) and redundanc\$3) and 365/\$7.ccls.)		